

March 1998

Radiation Hardened Non-Inverting, Octal, Three-State Buffer/Line Driver

Features

- QML Qualified Per MIL-PRF-38535 Requirements
- 1.25Micron Radiation Hardened SOS CMOS
- Radiation Environment
 - Latch-up Free Under any Conditions
 - Total Dose 3×10^5 RAD(SI)
 - SEU Immunity $<1 \times 10^{-10}$ Errors/Bit/Day
 - SEU LET Threshold >100MeV/(mg/cm²)
- Input Logic Levels . $V_{IL} = (0.3V)(V_{CC})$, $V_{IH} = (0.7V)(V_{CC})$
- Output Current..... $\pm 16mA$
- Quiescent Supply Current..... $20\mu A$
- Propagation Delay 9.0ns

Applications

- Databus Driving
- Data Routing
- Redundant Data Control Circuitry

Description

The Radiation Hardened ACS244MS is a Non-Inverting, Octal, Three-State Buffer/Line Driver with two active-LOW Enable inputs (\bar{AE} and \bar{BE}). Each Enable input controls four outputs. When an Enable input is LOW, the corresponding outputs are active. A HIGH on an Enable input causes the corresponding outputs to be high impedance, regardless of the input levels.

The ACS244MS is fabricated on a CMOS Silicon on Sapphire (SOS) process, which provides an immunity to Single Event Latch-up and the capability of highly reliable performance in any radiation environment. These devices offer significant power reduction and faster performance when compared to ALSTTL types.

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed below must be used when ordering.

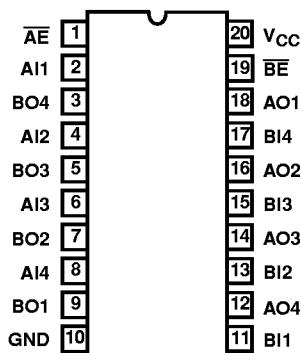
**Detailed Electrical Specifications for the ACS244 are contained in SMD 5962-98541. A "hot-link" is provided on our homepage with instructions for downloading.
<http://www.semi.harris.com/data/sm/index.htm>**

Ordering Information

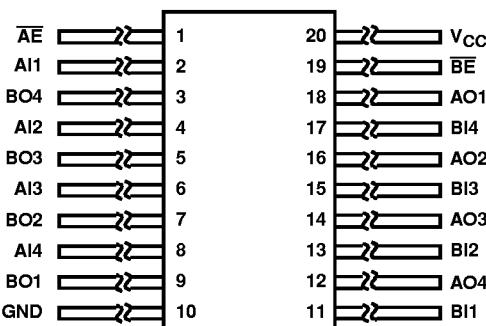
SMD PART NUMBER	HARRIS PART NUMBER	TEMP. RANGE (°C)	PACKAGE	CASE OUTLINE
5962F9854101VRC	ACS244DMSR-02	-55 to 125	20 Ld SBDIP	CDIP2-T20
N/A	ACS244D/Sample-02	25	20 Ld SBDIP	CDIP2-T20
5962F9854101VXC	ACS244KMSR-02	-55 to 125	20 Ld Flatpack	CDFP4-F20
N/A	ACS244K/Sample-02	25	20 Ld Flatpack	CDFP4-F20
N/A	ACS244HMSR-02	25	Die	N/A

Pinouts

ACS244 (SBDIP)
TOP VIEW



ACS244 (FLATPACK)
TOP VIEW



Die Characteristics**DIE DIMENSIONS:**Size: 2540 μm x 2540 μm (100 mils x 100mils)Thickness: 525 $\mu\text{m} \pm 25\mu\text{m}$ (20.6 mils ± 1 mil)Bond Pad: 110 μm x 110 μm (4.3 x 4.3 mils)**METALLIZATION: Al**Metal 1 Thickness: 0.7 $\mu\text{m} \pm 0.1\mu\text{m}$ Metal 2 Thickness: 1.0 $\mu\text{m} \pm 0.1\mu\text{m}$ **SUBSTRATE POTENTIAL:**

Unbiased Insulator

PASSIVATION

Type: Phosphorous Silicon Glass (PSG)

Thickness: 1.30 $\mu\text{m} \pm 0.15\mu\text{m}$ **SPECIAL INSTRUCTIONS:**Bond V_{CC} First**ADDITIONAL INFORMATION:**Worst Case Density: <2.0 x 10⁵ A/cm²

Transistor Count: 214

Metallization Mask Layout

ACS244MS

